

7MBR100XNA120-50

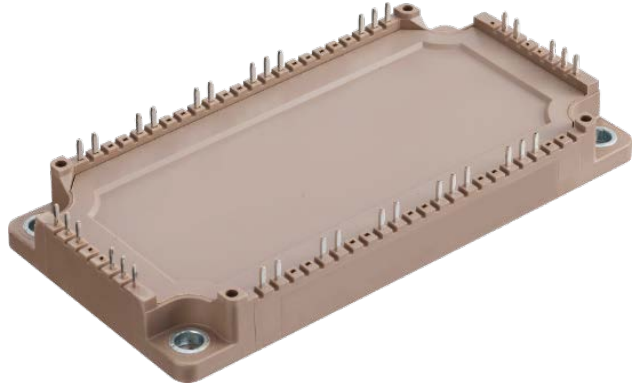
IGBT Modules

Power Module(X series)
1200V / 100A / PIM

Features

- LOW $V_{CE(sat)}$
- Compact Package
- P.C.Board Mount Module
- Converter Diode Bridge Dynamic Brake Circuit
- RoHS compliant Product

Typical appearance

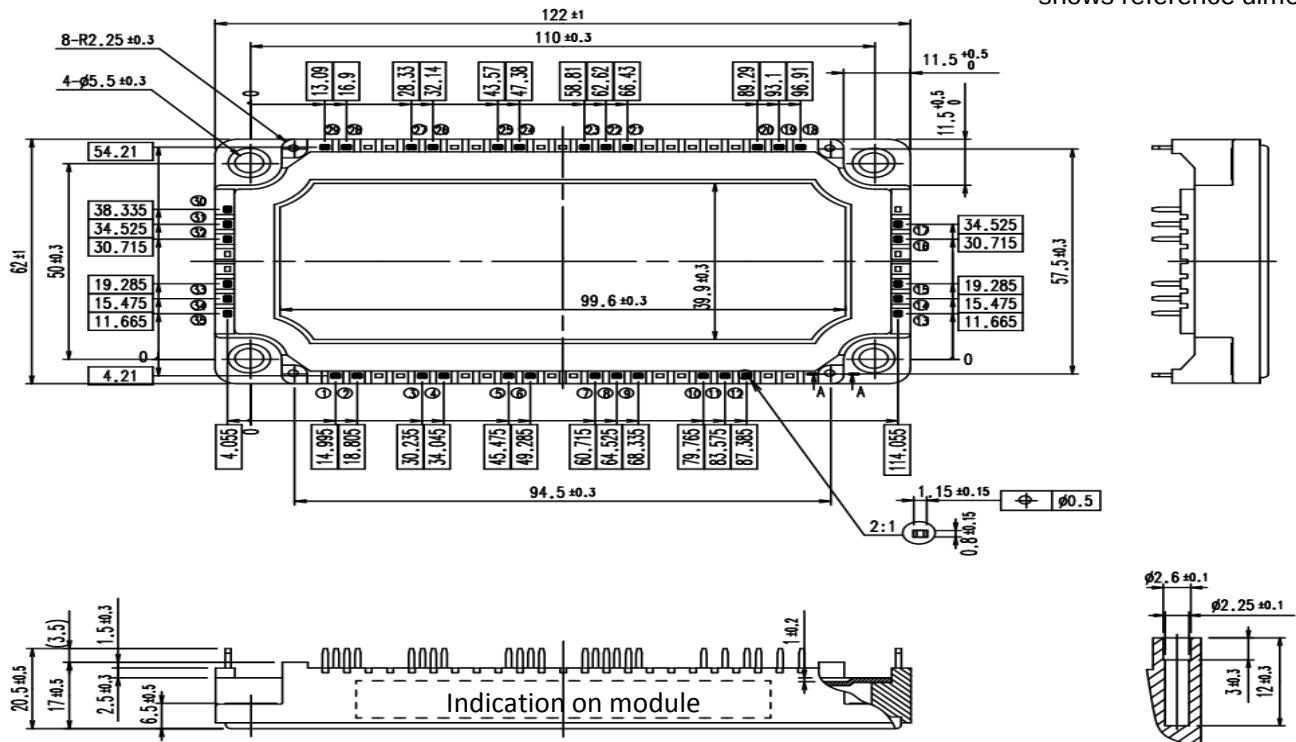


Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply

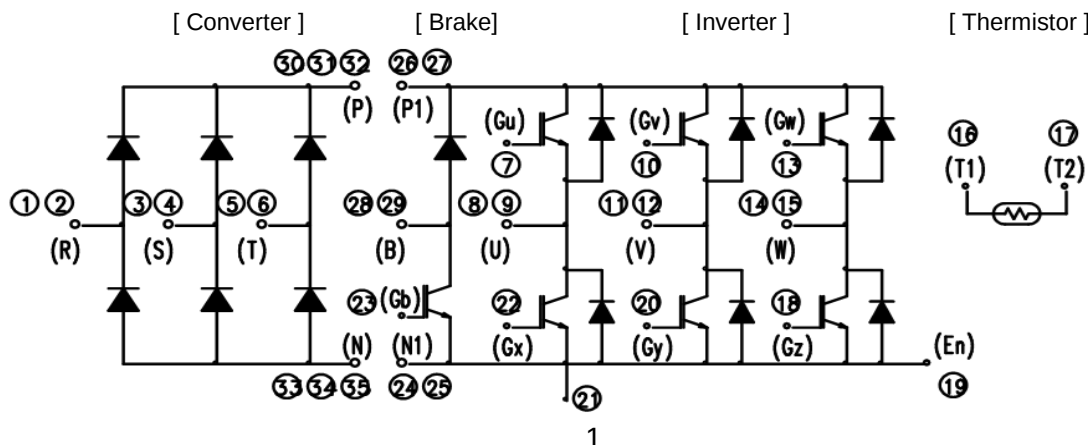
Outline drawing (Unit : mm)

□ shows theoretical dimension.
□ shows reference dimension.



Section A-A
Weight: 310 g (typ.)

Equivalent circuit



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IGBT Modules

□ Maximum ratings (at $T_c = 25^\circ\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V_{CES}			1200	V	
	Gate-Emitter voltage	V_{GES}			±20	V	
	Collector current	I_C	Continuous	$T_c=100^{\circ}\text{C}$	100	A	
		I_C pulse	1ms		200		
	Forward current	I_F	Continuous		100		
		I_F pulse	1ms		200		
Collector power dissipation		P_C	1 device		445	W	
Brake IGBT	Collector-Emitter voltage	V_{CES}			1200	V	
	Gate-Emitter voltage	V_{GES}			±20	V	
	Collector current	I_C	Continuous	$T_c=100^{\circ}\text{C}$	75	A	
		I_C pulse	1ms		150		
	Collector power dissipation		P_C	1 device		335	W
Brake FWD	Forward current	I_F	Continuous		35	A	
		I_{FRM}	1ms		70		
	Repetitive peak reverse voltage		V_{RRM}			1200	V
Converter	Repetitive peak reverse voltage		V_{RRM}			1600	V
	Average output current	I_O	Three-phase full wave rectified current	$T_c=80^{\circ}\text{C}$	100	A	
	Surge current (Non-Repetitive) (*1)	I_{FSM}	$t=10\text{ms}$, Half sine wave form	$T_{vj}=25^{\circ}\text{C}$	945	A	
				$T_{vj}=150^{\circ}\text{C}$	775		
I^2t (Non-Repetitive) (*1)	I^2t	$T_{vj}=25^{\circ}\text{C}$		4485	A ² s		
		$T_{vj}=150^{\circ}\text{C}$		3000			
Junction temperature		T_{vj}	Inverter, Brake		175	°C	
			Converter		150		
Operating junction temperature (under switching conditions)		T_{vjop}	Inverter, Brake		175		
			Converter		150		
Case temperature		T_c			125		
Storage temperature		T_{stg}			-40 ~ 125		
Isolation voltage	between terminals and copper base (*2)	V_{iso}	A.C. : 1min.		2500	Vrms	
	between thermistor and others (*3)						
Screw torque (*4)	Mounting	-	M5		6.0	N·m	

(*1) T_{vj} : Temperature at test start.

(*2) All terminals should be connected together during the test.

(*3) Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

(*4) Recommendable value : Mounting 2.5 ~ 6.0 N·m (M5)

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□ **Electrical characteristics** (at $T_{vj} = 25^{\circ}\text{C}$ unless otherwise specified)

Items		Symbols	Conditions		Characteristics			Units
					min.	typ.	max.	
Inverter	Zero Gate voltage collector current	I_{CES}	$V_{GE} = 0V$ $V_{CE} = 1200V$		-	-	50	μA
	Gate-Emitter leakage current	I_{GES}	$V_{CE} = 0V \quad V_{GE} = +20/-20V$		-	-	100	nA
	Gate-Emitter threshold voltage	$V_{GE(th)}$	$V_{CE} = 20V$ $I_C = 100mA$		6.0	6.5	7.0	V
	Collector-Emitter saturation voltage	$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 100A$	$T_{vj}=25^{\circ}C$	-	1.70	2.20	V
		$V_{CE(sat)}$ (chip)		$T_{vj}=25^{\circ}C$	-	1.45	1.90	
				$T_{vj}=125^{\circ}C$	-	1.80	-	
				$T_{vj}=150^{\circ}C$	-	1.85	-	
				$T_{vj}=175^{\circ}C$	-	1.90	-	
	Internal Gate resistance	r_g	-		-	5.6	-	Ω
	Capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0V, f = 1MHz$		-	11.6	-	nF
		C_{oes}			-	0.40	-	
		C_{res}			-	0.10	-	
	Gate charge	Q_G	$V_{CC} = 600V \quad V_{GE} = -15 \rightarrow +15V$ $I_C = 100A$		-	740	-	nC
	Forward voltage	V_F (terminal)	$I_F = 100A$	$T_{vj}=25^{\circ}C$	-	2.05	2.55	V
		V_F (chip)		$T_{vj}=25^{\circ}C$	-	1.80	2.25	
				$T_{vj}=125^{\circ}C$	-	1.85	-	
				$T_{vj}=150^{\circ}C$	-	1.80	-	
$T_{vj}=175^{\circ}C$				-	1.75	-		
Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600V$ $I_C, I_F = 100A \quad L_s = 30nH$ $V_{GE} = +15/-15 V$ $R_G = 5.1 \Omega$	$T_{vj}=25^{\circ}C$	-	0.21	-	μs	
			$T_{vj}=125^{\circ}C$	-	0.25	-		
			$T_{vj}=150^{\circ}C$	-	0.25	-		
			$T_{vj}=175^{\circ}C$	-	0.26	-		
	t_r	$V_{CC} = 600V$ $I_C, I_F = 100A \quad L_s = 30nH$ $V_{GE} = +15/-15 V$ $R_G = 5.1 \Omega$	$T_{vj}=25^{\circ}C$	-	0.05	-		
			$T_{vj}=125^{\circ}C$	-	0.06	-		
			$T_{vj}=150^{\circ}C$	-	0.06	-		
			$T_{vj}=175^{\circ}C$	-	0.06	-		
	$t_{d(off)}$	$V_{CC} = 600V$ $I_C, I_F = 100A \quad L_s = 30nH$ $V_{GE} = +15/-15 V$ $R_G = 5.1 \Omega$	$T_{vj}=25^{\circ}C$	-	0.29	-		
			$T_{vj}=125^{\circ}C$	-	0.32	-		
			$T_{vj}=150^{\circ}C$	-	0.33	-		
			$T_{vj}=175^{\circ}C$	-	0.34	-		
	t_f	$V_{CC} = 600V$ $I_C, I_F = 100A \quad L_s = 30nH$ $V_{GE} = +15/-15 V$ $R_G = 5.1 \Omega$	$T_{vj}=25^{\circ}C$	-	0.10	-		
			$T_{vj}=125^{\circ}C$	-	0.16	-		
			$T_{vj}=150^{\circ}C$	-	0.18	-		
			$T_{vj}=175^{\circ}C$	-	0.20	-		
Reverse recovery time	t_{rr}	$V_{CC} = 600V$ $I_C, I_F = 100A \quad L_s = 30nH$ $V_{GE} = +15/-15 V$ $R_G = 5.1 \Omega$	$T_{vj}=25^{\circ}C$	-	0.11	-		
			$T_{vj}=125^{\circ}C$	-	0.18	-		
			$T_{vj}=150^{\circ}C$	-	0.22	-		
			$T_{vj}=175^{\circ}C$	-	0.25	-		

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$

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IGBT Modules

Items		Symbols	Conditions		Characteristics			Units
					min.	typ.	max.	
Inverter	Switching loss (per pulse)	E_{on}	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	7.45	-	mJ
			$I_C, I_F = 100A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	10.51	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	11.50	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	12.79	-	
		E_{off}	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	7.07	-	
			$I_C, I_F = 100A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	8.82	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	9.55	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	9.93	-	
		E_{rr}	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	3.00	-	
			$I_C, I_F = 100A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	4.88	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	5.88	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	6.51	-	
Zero Gate voltage collector current		I_{CES}	$V_{GE} = 0V$ $V_{CE} = 1200V$		-	-	50	μA
Gate-Emitter leakage current		I_{GES}	$V_{CE} = 0V, \ V_{GE} = +20/-20V$		-	-	100	nA
Collector-Emitter saturation voltage		$V_{CE(sat)}$ (terminal)	$V_{GE} = 15V$ $I_C = 75A$	$T_{vj}=25^{\circ}C$	-	1.70	2.15	V
		$V_{CE(sat)}$ (chip)		$T_{vj}=25^{\circ}C$	-	1.50	1.95	
				$T_{vj}=125^{\circ}C$	-	1.85	-	
				$T_{vj}=150^{\circ}C$	-	1.95	-	
				$T_{vj}=175^{\circ}C$	-	2.00	-	
Internal Gate resistance		r_g	-		-	8	-	Ω
Brake	Switching time (*1)	$t_{d(on)}$	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	0.18	-	μs
			$I_C = 75A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	0.21	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	0.21	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	0.22	-	
		t_r	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	0.04	-	
			$I_C = 75A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	0.05	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	0.05	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	0.05	-	
		$t_{d(off)}$	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	0.25	-	
			$I_C = 75A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	0.28	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	0.29	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	0.29	-	
		t_f	$V_{CC} = 600V$	$T_{vj}=25^{\circ}C$	-	0.12	-	
			$I_C = 75A \ L_s = 30nH$	$T_{vj}=125^{\circ}C$	-	0.18	-	
			$V_{GE} = +15/-15 \ V$	$T_{vj}=150^{\circ}C$	-	0.20	-	
			$R_G = 5.1 \ \Omega$	$T_{vj}=175^{\circ}C$	-	0.21	-	
		Reverse current		I_{RRM}	$V_R = 1200V$		-	
Forward voltage	V_F (terminal)	$I_F = 35A$	$T_{vj}=25^{\circ}C$	-	2.00	2.45	V	
	V_F (chip)	$I_F = 35A$	$T_{vj}=25^{\circ}C$	-	1.80	2.25		
			$T_{vj}=125^{\circ}C$	-	1.85	-		
			$T_{vj}=150^{\circ}C$	-	1.80	-		
			$T_{vj}=175^{\circ}C$	-	1.75	-		
Reverse current	I_{RRM}	$V_R = 1600V$		-	-	50	μA	
Forward voltage	V_{FM}	$I_F = 100A$	terminal	-	1.30	1.80	V	
			chip	-	1.05	1.50		
Thermistor	Resistance	R	$T = 25^{\circ}C$		-	5000	-	Ω
			$T = 100^{\circ}C$		465	495	520	
	B value		B	$T = 25/ 50^{\circ}C$		3305	3375	3450

(*1) Turn on time (t_{on}) = $t_{d(on)} + t_r$, Turn off time (t_{off}) = $t_{d(off)} + t_f$
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IGBT Modules
NOTICE:

The external gate resistance (R_G) shown above is one of our recommended value for the purpose of minimum switching loss. However the optimum R_G depends on circuit configuration and/or environment. We recommend that the R_G has to be carefully chosen based on consideration if IGBT module matches design criteria, for example, switching loss, EMC/EMI, spike voltage, surge current and no unexpected oscillation and so on.

□ Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	$R_{th(j-c)}$	Inverter IGBT	-	-	0.34	°C/W
		Inverter FWD	-	-	0.45	
		Brake IGBT	-	-	0.45	
		Brake FWD	-	-	0.86	
		Converter Diode	-	-	0.47	
Contact thermal resistance (1 IGBT+1 FWD) (*1)	$R_{th(c-f)}$	with 1 W/(m·K) thermal grease	-	0.05	-	

(*1) This is the value which is defined mounting on the additional cooling fin with thermal grease.

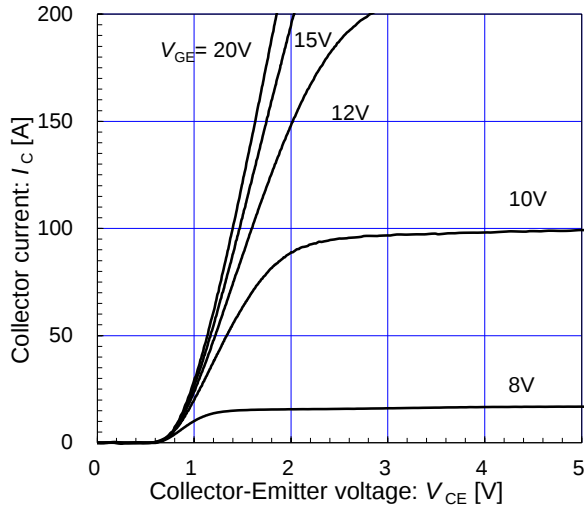
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IGBT Modules

[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

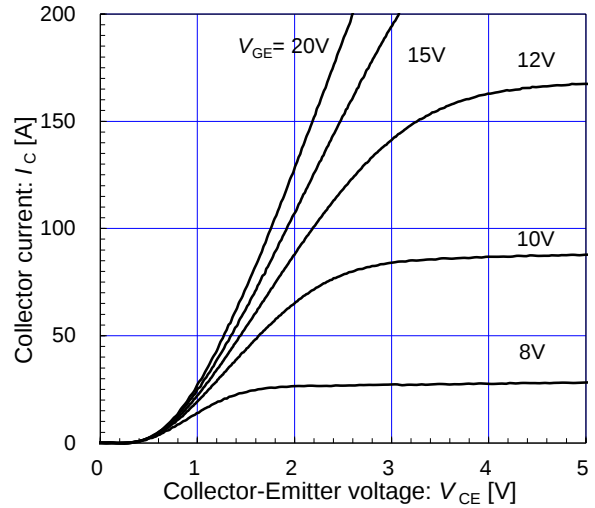
$T_{vj} = 25^{\circ}\text{C}$ / chip



[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

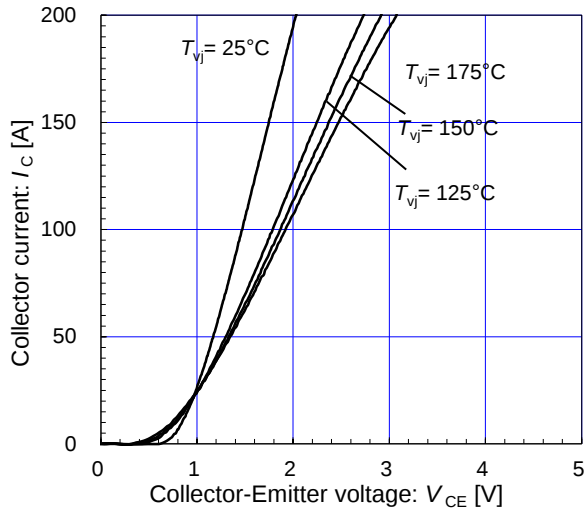
$T_{vj} = 175^{\circ}\text{C}$ / chip



[Inverter]

Collector current vs. Collector-Emittor voltage (typ.)

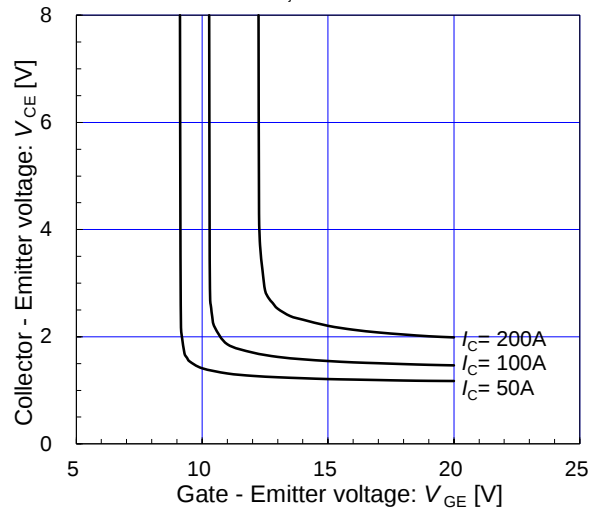
$V_{GE} = 15\text{V}$ / chip



[Inverter]

Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)

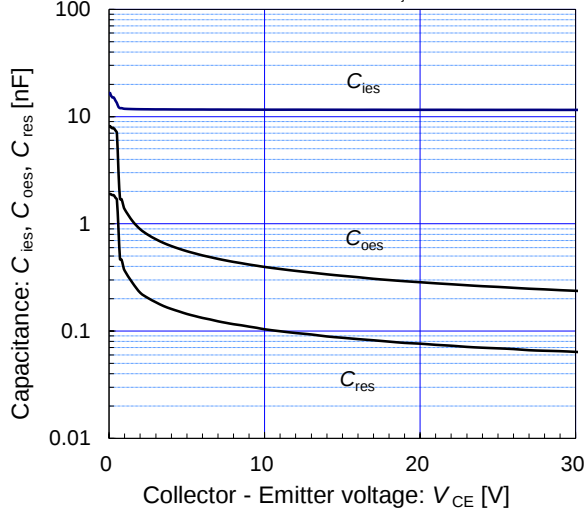
$T_{vj} = 25^{\circ}\text{C}$ / chip



[Inverter]

Capacitance vs. Collector-Emittor voltage (typ.)

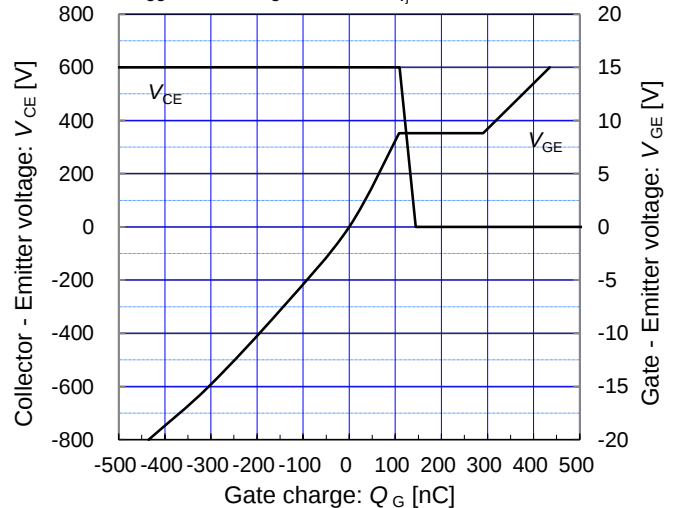
$V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_{vj} = 25^{\circ}\text{C}$



[Inverter]

Dynamic Gate charge (typ.)

$V_{CC} = 600\text{V}$, $I_c = 100\text{A}$, $T_{vj} = 25^{\circ}\text{C}$



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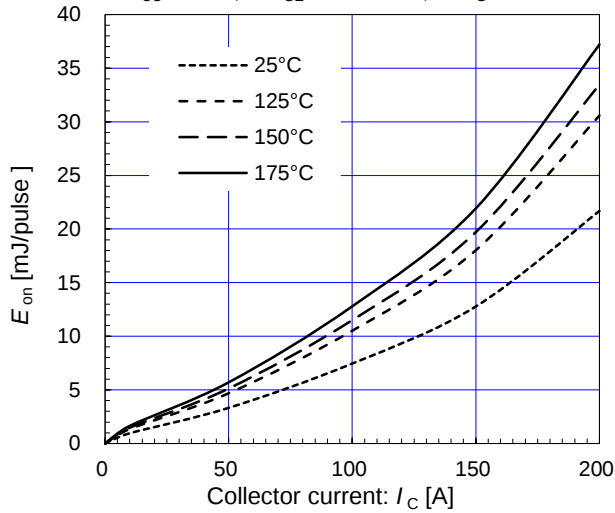
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IGBT Modules

[Inverter]

E_{on} vs. Collector current (typ.)

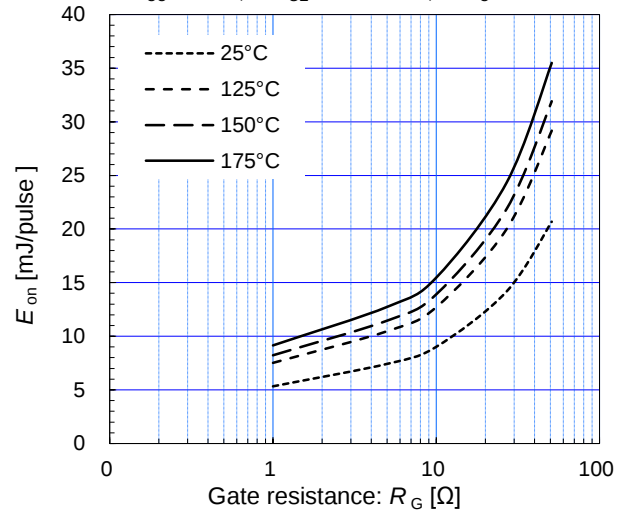
$V_{CC}=600V$, $V_{GE}=+15/-15V$, $R_G=5.1\Omega$



[Inverter]

E_{on} vs. Gate resistance (typ.)

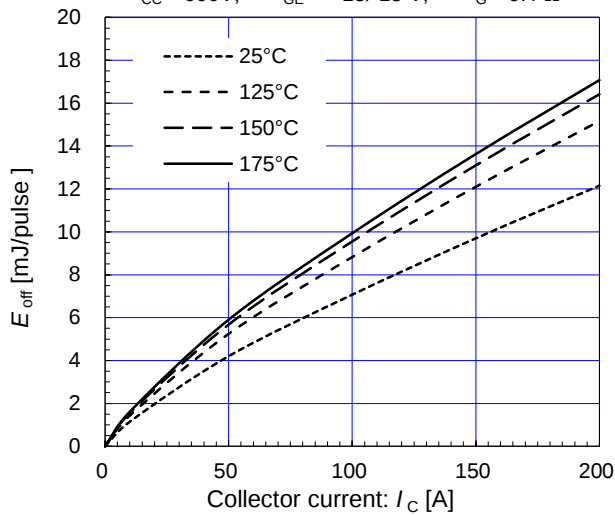
$V_{CC}=600V$, $V_{GE}=+15/-15V$, $I_C=100A$



[Inverter]

E_{off} vs. Collector current (typ.)

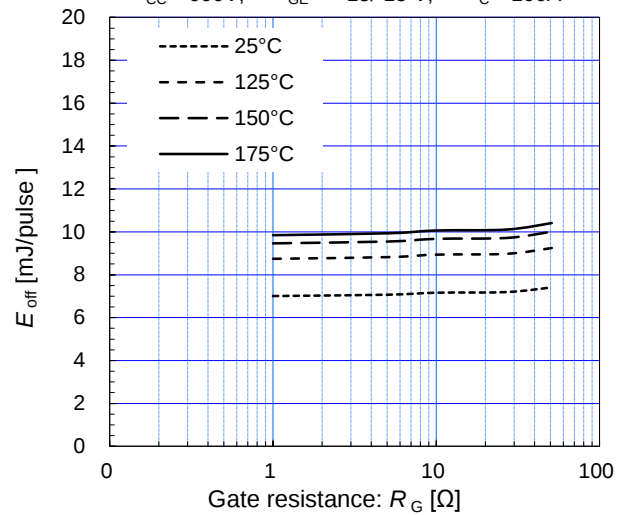
$V_{CC}=600V$, $V_{GE}=+15/-15V$, $R_G=5.1\Omega$



[Inverter]

E_{off} vs. Gate resistance (typ.)

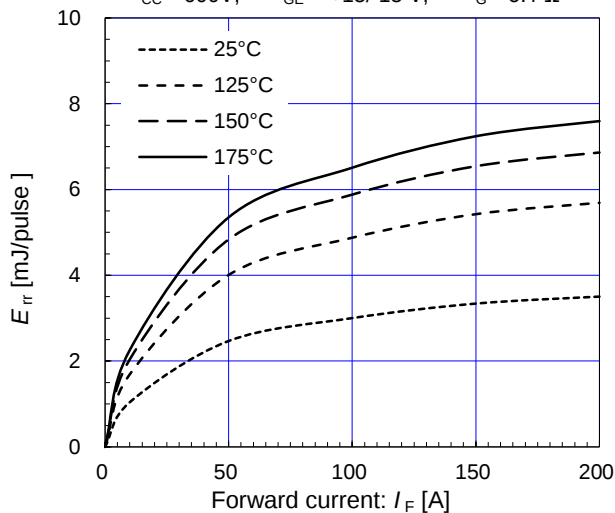
$V_{CC}=600V$, $V_{GE}=+15/-15V$, $I_C=100A$



[Inverter]

E_{rr} vs. Forward current (typ.)

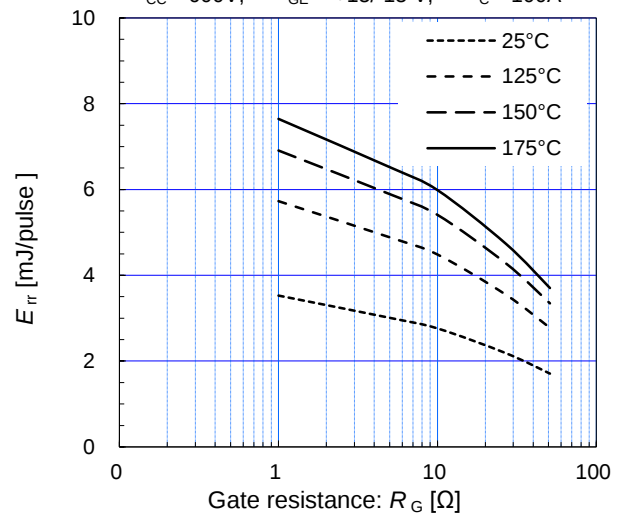
$V_{CC}=600V$, $V_{GE}=+15/-15V$, $R_G=5.1\Omega$



[Inverter]

E_{rr} vs. Gate resistance (typ.)

$V_{CC}=600V$, $V_{GE}=+15/-15V$, $I_C=100A$



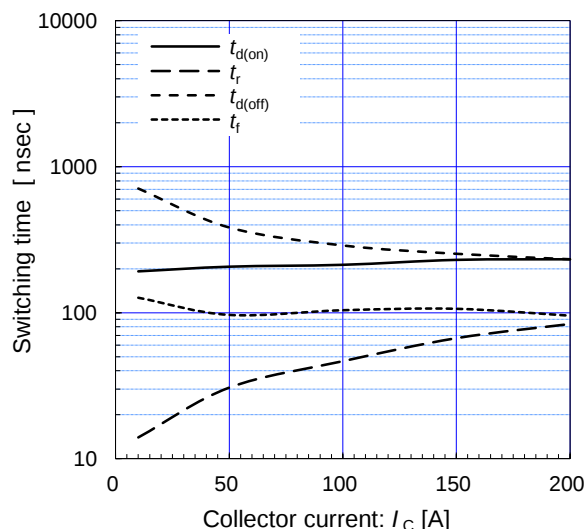
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IGBT Modules

[Inverter]

Switching time vs. Collector current (typ.)

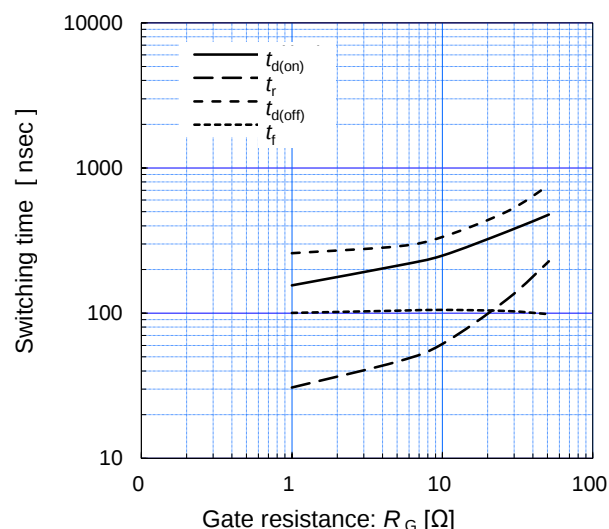
$V_{CC}=600V$, $R_G=5.1\Omega$ $V_{GE}=+15/-15V$, $T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

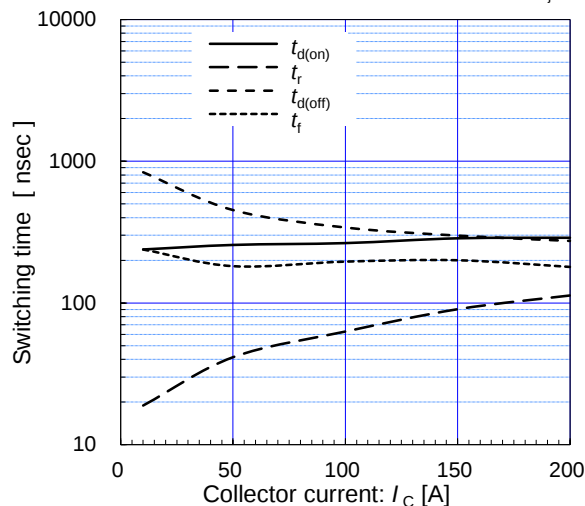
$V_{CC}=600V$, $I_C=100A$, $V_{GE}=+15/-15V$, $T_{vj}=25^\circ C$



[Inverter]

Switching time vs. Collector current (typ.)

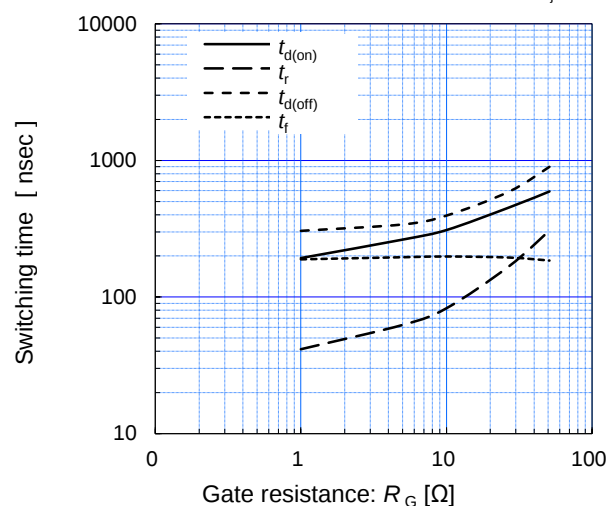
$V_{CC}=600V$, $R_G=5.1\Omega$ $V_{GE}=+15/-15V$, $T_{vj}=175^\circ C$



[Inverter]

Switching time vs. Gate resistance (typ.)

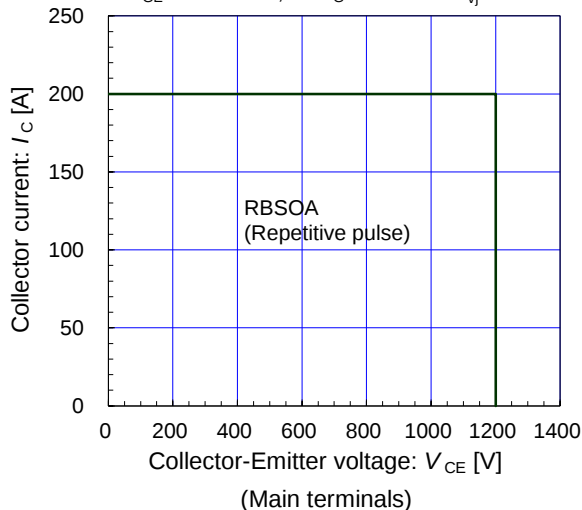
$V_{CC}=600V$, $I_C=100A$, $V_{GE}=+15/-15V$, $T_{vj}=175^\circ C$



[Inverter]

Reverse bias safe operating area (max.)

$V_{GE}=+15/-15V$, $R_G \geq 5.1\Omega$ $T_{vj}=175^\circ C$

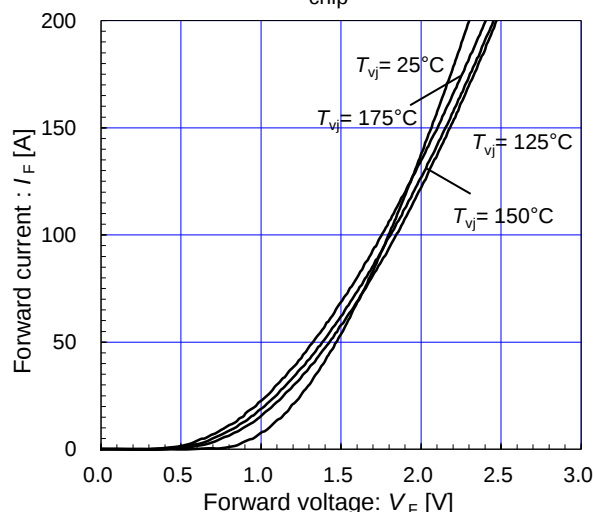


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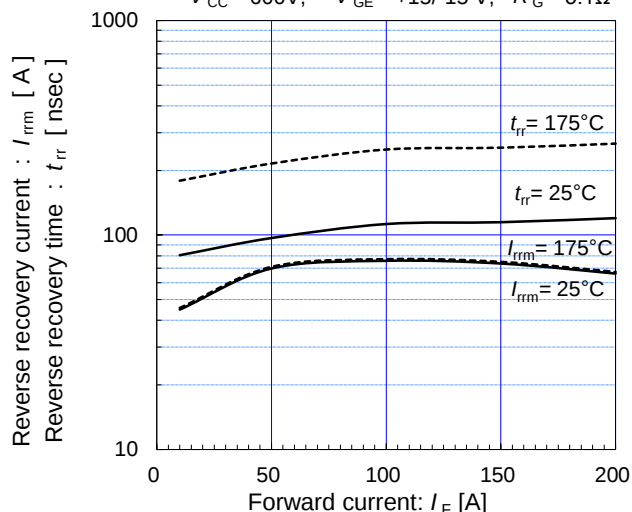
[Inverter]

Forward current vs. Forward voltage (typ.)
chip



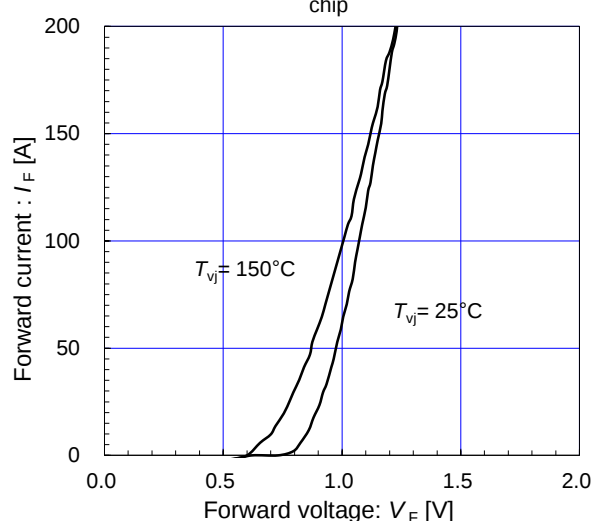
[Inverter]

Reverse recovery characteristics (typ.)
 $V_{CC} = 600V$, $V_{GE} = +15/-15V$, $R_G = 5.1\Omega$

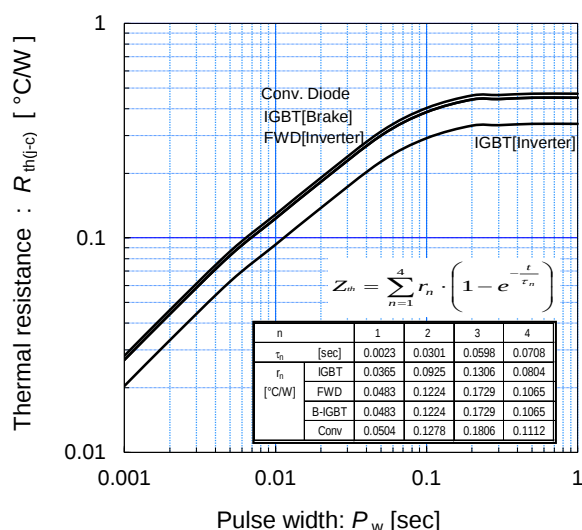


[Converter]

Forward current vs. Forward voltage (typ.)
chip

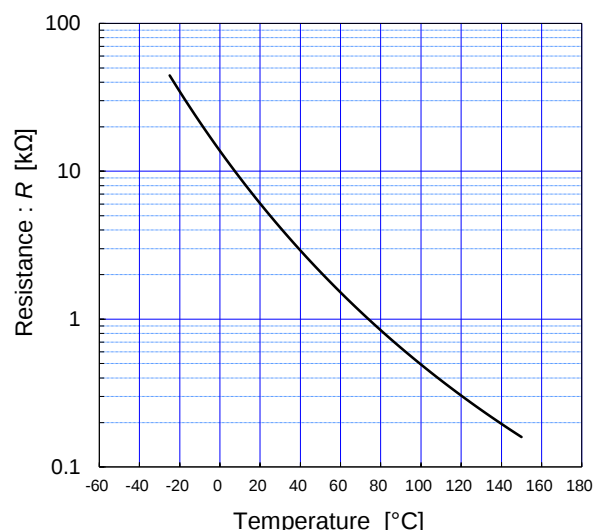


Transient thermal resistance (max.)



[Thermistor]

Temperature characteristic (typ.)



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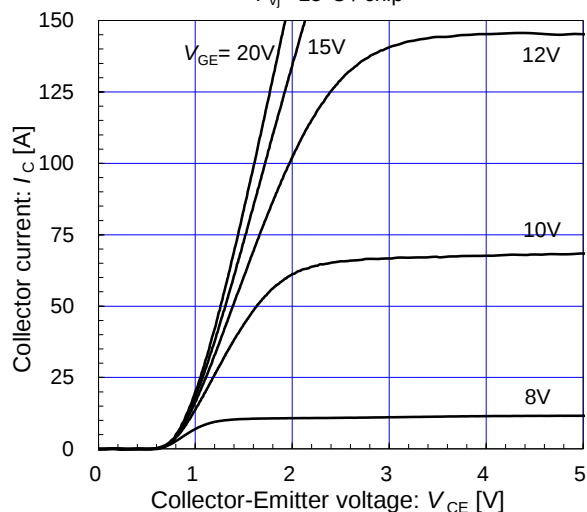
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IGBT Modules

[Brake]

Collector current vs. Collector-Emittor voltage (typ.)

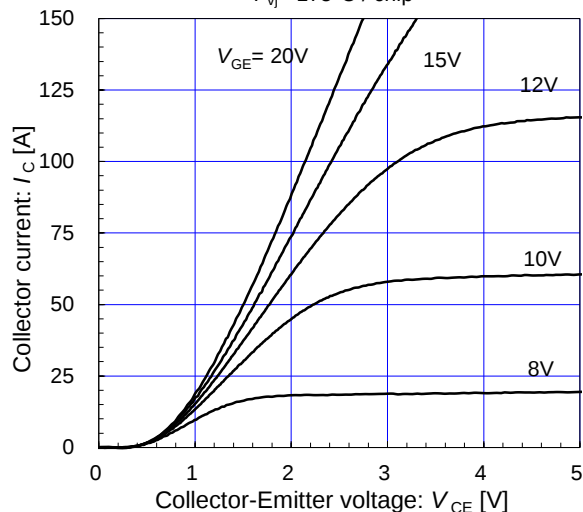
$T_{vj} = 25^{\circ}\text{C}$ / chip



[Brake]

Collector current vs. Collector-Emittor voltage (typ.)

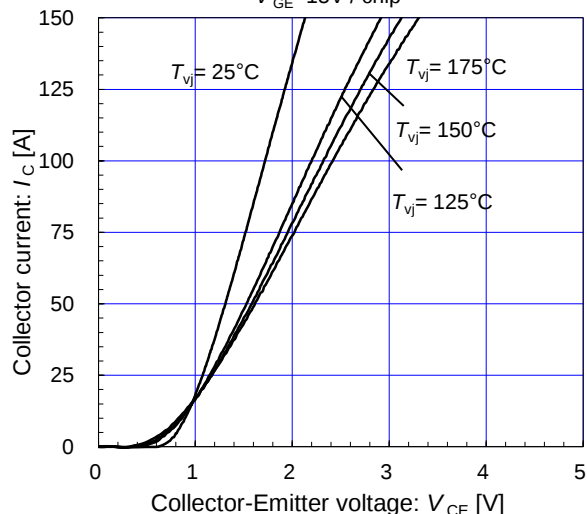
$T_{vj} = 175^{\circ}\text{C}$ / chip



[Brake]

Collector current vs. Collector-Emittor voltage (typ.)

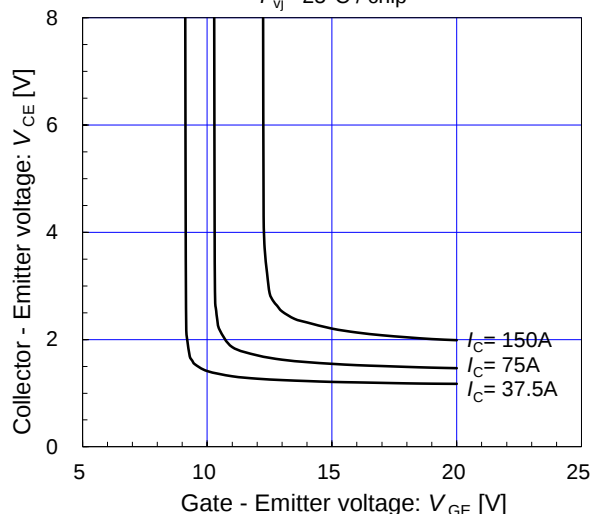
$V_{GE} = 15\text{V}$ / chip



[Brake]

Collector-Emittor voltage vs. Gate-Emittor voltage (typ.)

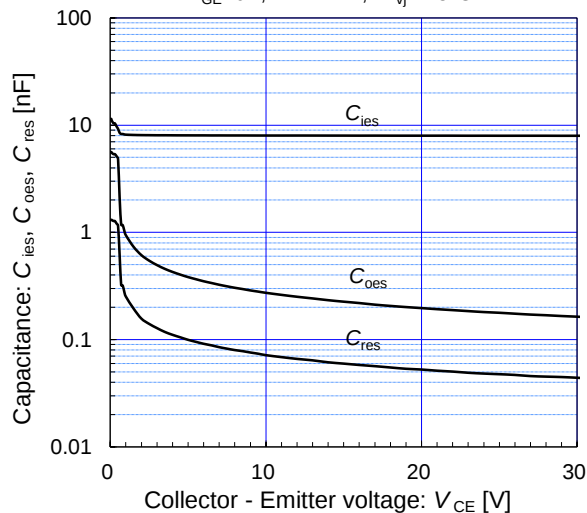
$T_{vj} = 25^{\circ}\text{C}$ / chip



[Brake]

Capacitance vs. Collector-Emittor voltage (typ.)

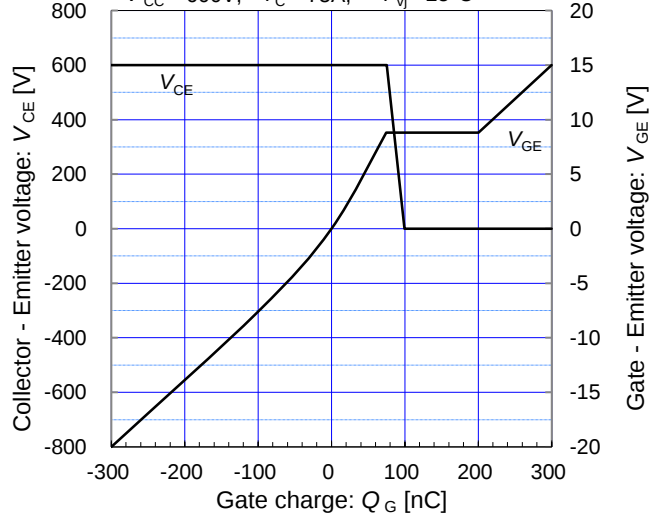
$V_{GE} = 0\text{V}$, $f = 1\text{MHz}$, $T_{vj} = 25^{\circ}\text{C}$



[Brake]

Dynamic Gate charge (typ.)

$V_{CC} = 600\text{V}$, $I_c = 75\text{A}$, $T_{vj} = 25^{\circ}\text{C}$



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